

RADIATION-INDUCED REARRANGEMENT  
OF DEFECTS IN SILICON CRYSTALS

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S u m m a r y

Physical and mathematical models of the radiation-induced ordering of a defect structure in silicon crystals are proposed. These models involve an increase of the diffusion coefficient of interstitial silicon in the irradiation field and a reduction of the defect lifetime at irradiation doses below 260 Gy. Free surfaces of crystals, phase interfaces, and dislocations are considered to be effective defect sinks.